

Description

The AO3422-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

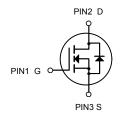
D G SOT23-3L

General Features

 $V_{DS} = 60V, I_{D} = 4.5A$

 $R_{DS(ON)} < 75 m\Omega$ @ $V_{GS}=10V$

 $R_{DS(ON)}$ < 90m Ω @ V_{GS} =4.5V



N-Channel MOSFET

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3422-HXY	SOT23-3L	ARDP 7B	3000PCS

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	60	V	
V _G s	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	4.5	А	
Ірм	Drain Current-Pulsed (Note 1)	15	А	
P _D	Maximum Power Dissipation	8	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Rеја	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
Б	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =5A		70	75	mΩ
R _{DS(ON)}		V _{GS} =4.5V , I _D =5A		80	90	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
1	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C			1	- uA
IDSS		V _{DS} =48V , V _{GS} =0V , T _J =55°C			5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =5A		7		S
Qg	Total Gate Charge (10V)			5.5		
Q _{gs}	Gate-Source Charge	V _{DS} =12V , V _{GS} =10V , I _D =5A		1.8		nC
Q_{gd}	Gate-Drain Charge			2.4		
T _{d(on)}	Turn-On Delay Time			6		
Tr	Rise Time	V_{DD} =12V , V_{GS} =10V , R_{G} =3.3 Ω		10		
T _{d(off)}	Turn-Off Delay Time	I _D =5A		15		ns
T _f	Fall Time			7		
Ciss	Input Capacitance			695		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		148		pF
Crss	Reverse Transfer Capacitance			7		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,5}	V- V- OV Force Current			17	Α
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			50	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.1mH, I_{AS} =15A

^{4.}The power dissipation is limited by 150°C junction temperature

^{5.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

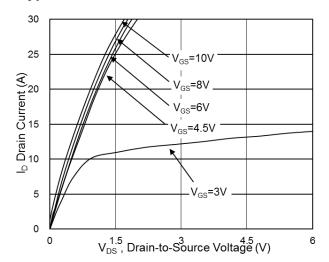


Fig.1 Typical Output Characteristics

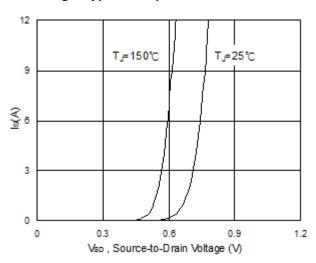


Fig.3 Forward Characteristics of Reverse

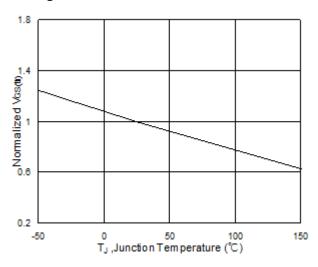


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

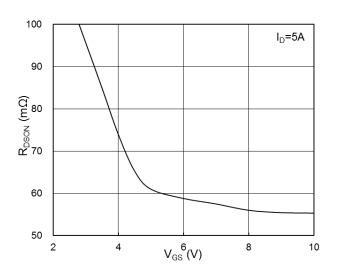


Fig.2 On-Resistance vs. Gate-Source Voltage

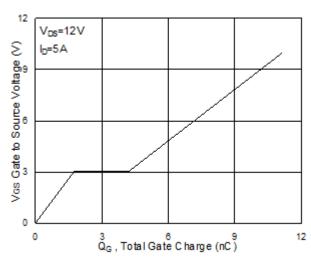


Fig.4 Gate-Charge Characteristics

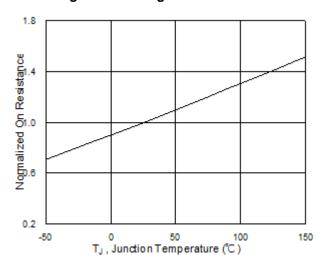
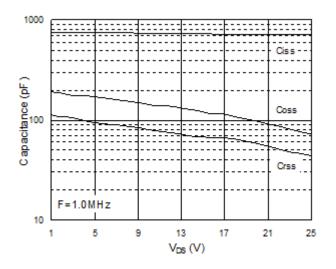


Fig.6 Normalized R_{DSON} vs. T_J



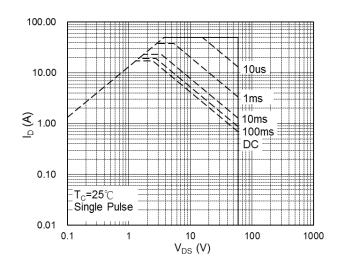


Fig.7 Capacitance

Fig.8 Safe Operating Area

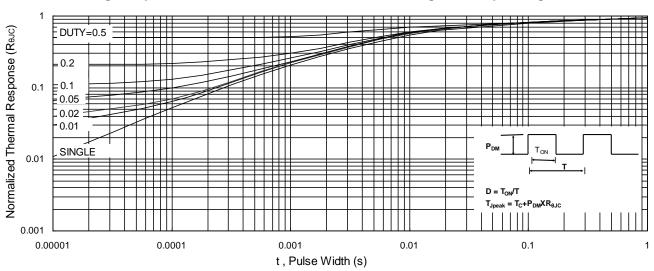


Fig.9 Normalized Maximum Transient Thermal Impedance

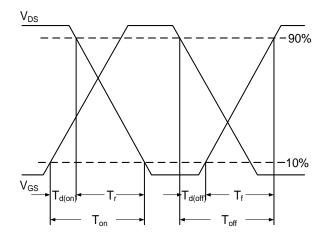


Fig.10 Switching Time Waveform

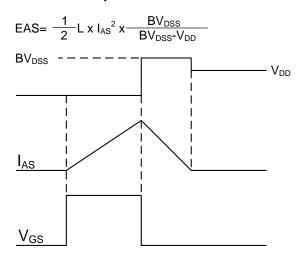
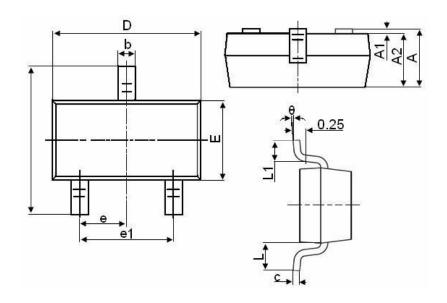


Fig.11 Unclamped Inductive Switching Waveform



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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